The 1N303 is a hermetically sealed silicon junction diode designed for general purpose applications and providing extreme stability, wide temperature range, high back resistance (100 megohms or more), and high ratio of back to forward resistance. The flexible terminal leads may be soldered or welded directly to the terminals of circuit components without the use of sockets. Standard inline subminiature sockets may be used by cutting the leads to a suitable length.

MECHANICAL DATA
CASE: Metal and Glass
BASE: None (0.016" tinned duralm wire. Length: 1.0" min.
Spacing: 0.080" center-to-center)
TERMINAL CONNECTIONS: (Black Dot is adjacent to Cathode Terminal)
MOUNTING POSITION: Any

ELECTRICAL DATA
RATINGS - ABSOLUTE MAXIMUM VALUES: (at 25°C)
- Peak Inverse Voltage: 125 volts
- Continuous Inverse Voltage: 110 volts
- Average Rectified Current: 30 ma.
- Average Rectified Current (100°C): 10 ma.
- Peak Rectified Current: 100 ma.
- Surge Current (for 1 sec.): 300 ma.
- Ambient Temperature Range: -55 to +150 °C
- Dissipation at:
  - 25°C: 150 mw.
  - 65°C: 60 mw.
  - 100°C: 20 mw.
  - 150°C: 10 mw.

CHARACTERISTICS:
- Maximum Inverse Current at -10 volts: 0.2 µA
- Maximum Inverse Current at -100 volts: 0.1 µA
- Minimum Forward Current at +1.0 volt: 3 ma.